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20 and ((pattern\$3 or etch\$3) adj2 (organic or polymer)).cjm.

No.	P	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	F	C	P	S	T	D
1	P	A1	US 20030224611	20031204	60	Manufacturing method of semiconductor devices by using Manufacturing use of	438/706			Seta, Shoji et al.						US 2003
2	P	A1	US 20030207521	20031106	56	Method of manufacturing electronic device	438/200			Tanaka, Toshihiko et al.						US 2003
3	P	A1	US 20030165750	20030904	29	Aperture masks for circuit fabrication	430/5	430/22; 430/311		Tanaka, Toshihiko et al.						US 2003
4	P	A1	US 20030151118	20030814	18	METHOD FOR PRODUCING ACTIVE OR PASSIVE COMPONENTS ON A P	257/620	257/40; 257/618;		Baudes, Paul F. et al.						US 2003
5	P	A1	US 20030052081	20030320	6	Computing device with roll up components	216/24			KOOPS, HANS WILFRIED PETER						US 2003
6	P	A1	US 20030046256	20030313	30	Method for manufacturing a semiconductor device	345/168			Salmon, Peter C.						US 2003
7	P	A1	US 20030036293	20030220	31	Nonvolatile semiconductor memory device and manufacture	438/780	438/781; 438/942		Tanaka, Toshihiko et al.						US 2003
8	P	A1	US 20030022446	20030130	18	Fabrication-of-molecular-electronic circuit by imprint	438/257	257/315; 257/e21.682;		Lee, Seong-Soo et al.						US 2003
9	P	A1	US 20030003715	20030102	9	Electronically active primer layers for thermal patterning	438/800			Chen, Yong						US 2003
10	P	A1	US 20020086232	20020704	13	Manufacturing method of semiconductor devices by using Method of manufacturing a semiconductor device	430/200	430/311; 430/312; 117/84;		Nirmal, Manoj et al.						US 2002
11	P	A1	US 20020059899	20020523	60	Nonvolatile semiconductor memory device and manufacture	117/97	257/E21.252;		Seta, Shoji et al.						US 2002
12	P	A1	US 20020052122	20020502	56	Method for manufacturing a semiconductor device	438/758			Tanaka, Toshihiko et al.						US 2002
13	P	A1	US 20010015454	20010823	19	Manufacturing use of photomasks with an opaque pattern	257/315	257/314; 257/316;		Lee, Seong-soo et al.						US 2001
14	P	A1	US 6645856 B2	20031111	30	Method for manufacturing a semiconductor device using h	438/671	430/313; 430/5;		Tanaka, Toshihiko et al.						US 664
15	P	A1	US 6605442 B2	20030812	56	Manufacturing method of semiconductor devices by using	438/700	257/E21.252; 257/E21.579;		Seta, Shoji et al.						US 660
16	P	A1	US 6596656 B2	20030722	54	Manufacturing use of photomasks with an opaque pa		430/5; 438/945		Tanaka, Toshihiko et al.						US 659
17	P	A1	US 6580000 B2	20030624	18	Nonvolatile semiconductor memory device and manufacture	438/257	257/E21.682;		Lee, Seong-soo et al.						US 658

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